

AMENDMENTS TO THE SPECIFICATION:

Please amend the following paragraphs as indicated:

[0021] In the system achieved in the third aspect or in the method achieved in the fourth aspect, the measuring apparatus may be utilized to prepare measurement processing [[I]]information required in the measurement processing executed by the measuring unit at each processing apparatus so as to allow the measuring unit to execute the measurement processing based upon the measurement processing [[I]]information. By adopting such a structure, the measuring unit at each processing apparatus in the area is kept in a ready state for device production operation or the like at all times. As a result, the production capacity in the area is not compromised.

[0110] Next, model expression update processing executed in the process control system in the embodiment to update the recurrence expression (model expression) defined through the PLS method is explained in reference to the drawings. FIG. [[5]]Z presents a flowchart of the model expression update processing executed by the process control device 150.

[0123] In addition, an electric measuring instrument (e.g., a VI probe) may be installed at the matcher 241 or 251. VI probe data indicating the high-frequency voltage V, the high-frequency current I, the high-frequency phase P and the impedance Z of the higher harmonic wave attributable to the plasma generated by applying the high-frequency power P to the upper electrode 221 or the susceptor (the lower electrode) 205 which are obtained via the electric measuring instruments as the operation data.